

Thyristor Module

$$V_{RRM} = 2 \times 1200 \text{ V}$$

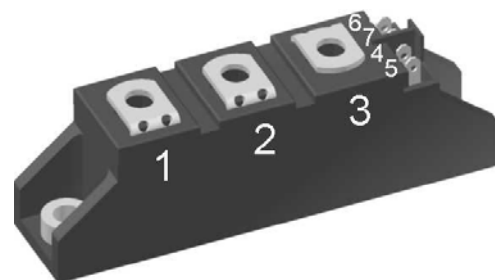
$$I_{TAV} = 140 \text{ A}$$

$$V_T = 1.28 \text{ V}$$

Phase leg

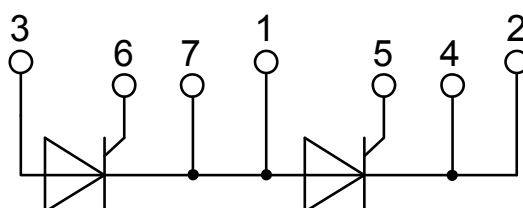
Part number

MCMA140P1200TA



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

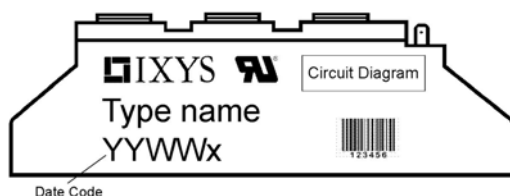
- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Thyristor				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
I_{RD}	reverse current, drain current	$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			100	μA
		$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 140^{\circ}\text{C}$			10	mA
V_T	forward voltage drop	$I_T = 150\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.29	V
		$I_T = 300\text{ A}$				1.63	V
		$I_T = 150\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.28	V
		$I_T = 300\text{ A}$				1.70	V
I_{TAV}	average forward current	$T_C = 85^{\circ}\text{C}$	$T_{VJ} = 140^{\circ}\text{C}$			140	A
$I_{T(RMS)}$	RMS forward current	180° sine				220	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 140^{\circ}\text{C}$			0.85	V
r_T	slope resistance					2.8	m Ω
R_{thJC}	thermal resistance junction to case					0.22	K/W
R_{thCH}	thermal resistance case to heatsink				0.20		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			520	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			2.40	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			2.59	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}\text{C}$			2.04	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			2.21	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			28.8	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			27.9	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}\text{C}$			20.8	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			20.2	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		119		pF
P_{GM}	max. gate power dissipation	$t_P = 30\text{ }\mu\text{s}$	$T_C = 140^{\circ}\text{C}$			10	W
		$t_P = 300\text{ }\mu\text{s}$				5	W
P_{GAV}	average gate power dissipation					0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 450\text{ A}$				150	A/ μs
		$t_P = 200\text{ }\mu\text{s}; di_G/dt = 0.45\text{ A}/\mu\text{s}$ non-repet., $I_T = 150\text{ A}$				500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $T_{VJ} = 140^{\circ}\text{C}$				1000	V/ μs
		$R_{GK} = \infty$; method 1 (linear voltage rise)					
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1.5	V
			$T_{VJ} = -40^{\circ}\text{C}$			1.6	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			150	mA
			$T_{VJ} = -40^{\circ}\text{C}$			200	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}\text{C}$			0.2	V
I_{GD}	gate non-trigger current					10	mA
I_L	latching current	$t_P = 10\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$			200	mA
		$I_G = 0.45\text{ A}; di_G/dt = 0.45\text{ A}/\mu\text{s}$					
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$			200	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}\text{C}$			2	μs
		$I_G = 0.45\text{ A}; di_G/dt = 0.45\text{ A}/\mu\text{s}$					
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 150\text{ A}; V_D = \frac{2}{3} V_{DRM}$ $T_{VJ} = 140^{\circ}\text{C}$ $di/dt = 10\text{ A}/\mu\text{s}; dv/dt = 20\text{ V}/\mu\text{s}; t_P = 200\text{ }\mu\text{s}$			185		μs

Package TO-240AA				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				200	A
T _{stg}	storage temperature			-40		125	°C
T _{VJ}	virtual junction temperature			-40		140	°C
Weight					90		g
M _D	mounting torque			2.5		4	Nm
M _T	terminal torque			2.5		4	Nm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA	4800			V
		t = 1 minute		4000			V
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal	13.0	9.7			mm
d _{Spb/App}		terminal to backside	16.0	16.0			mm



Part number

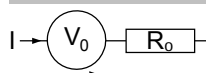
M = Module
 C = Thyristor (SCR)
 M = Thyristor
 A = (up to 1800V)
 140 = Current Rating [A]
 P = Phase leg
 1200 = Reverse Voltage [V]
 TA = TO-240AA-1B

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCMA140P1200TA	MCMA140P1200TA	Box	6	512625

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 140^{\circ}\text{C}$



Thyristor

$V_{0\max}$	threshold voltage	0.85	V
$R_{0\max}$	slope resistance *	1.6	mΩ

Technical drawing of a 5-hole metal plate. The drawing shows a side view with the following dimensions and labels:

- Overall width: 92 ± 0.5
- Distance from left edge to center of hole 1: 80 ± 0.3
- Distance between centers of holes 1 and 2: 10
- Distance between centers of holes 2 and 3: 10
- Distance between centers of holes 3 and 4: 10
- Distance between centers of holes 4 and 5: 10
- Distance from right edge to center of hole 5: 6
- Overall height: 20.8 ± 0.25
- Distance from top edge to center of hole 1: 14.8
- Distance from center of hole 1 to top edge: 10 ± 0.1
- Distance from center of hole 1 to bottom edge: 5.5 ± 0.1
- Distance from center of hole 1 to center of hole 2: 10
- Distance from center of hole 2 to center of hole 3: 10
- Distance from center of hole 3 to center of hole 4: 10
- Distance from center of hole 4 to center of hole 5: 10
- Distance from center of hole 5 to right edge: 6
- Distance from center of hole 1 to center of hole 3: 25 ± 0.3
- Distance from center of hole 1 to center of hole 5: 45 ± 0.3
- Distance from center of hole 1 to right edge: 65 ± 0.3
- Labels: 1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 11, 12, 13, 14, 15, 16, 17, 18, 19, 20, 21, 22, 23, 24, 25, 26, 27, 28, 29, 30, 31, 32, 33, 34, 35, 36, 37, 38, 39, 40, 41, 42, 43, 44, 45, 46, 47, 48, 49, 50, 51, 52, 53, 54, 55, 56, 57, 58, 59, 60, 61, 62, 63, 64, 65, 66, 67, 68, 69, 70, 71, 72, 73, 74, 75, 76, 77, 78, 79, 80, 81, 82, 83, 84, 85, 86, 87, 88, 89, 90, 91, 92, 93, 94, 95, 96, 97, 98, 99, 100

Thyristor

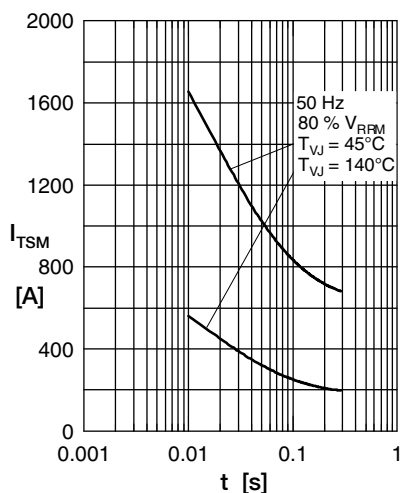


Fig. 1 Surge overload current
 I_{TSM} : Crest value, t : duration

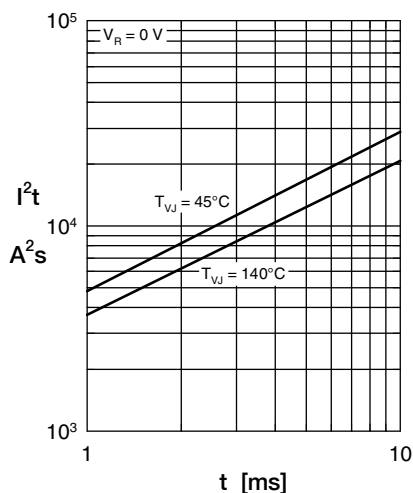


Fig. 2 I^2t versus time (1-10 ms)

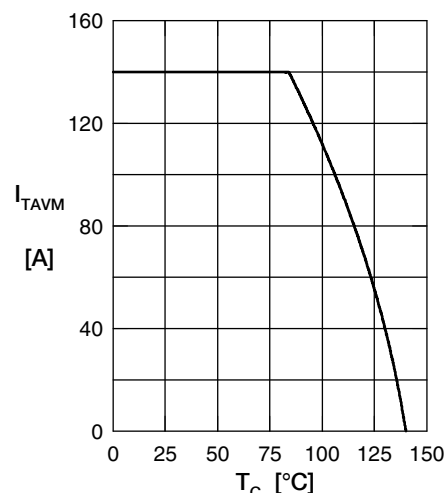


Fig. 3 Maximum forward current at case temperature

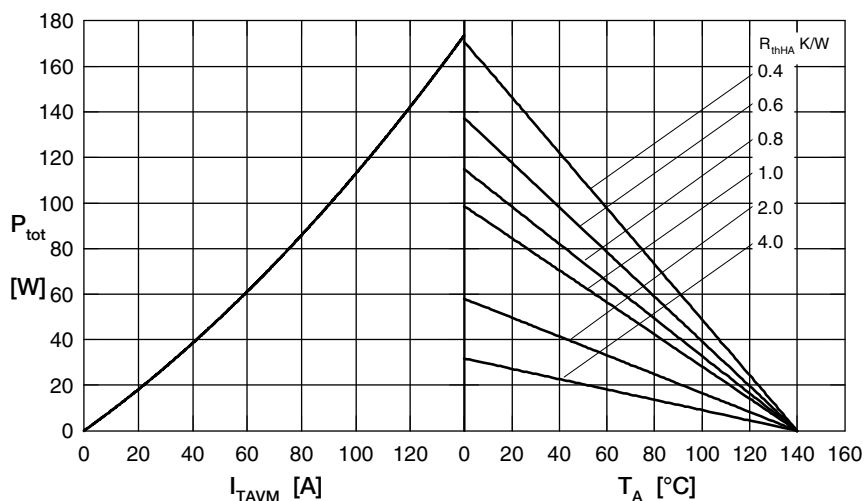


Fig. 4 Power dissipation vs. forward current and ambient temperature

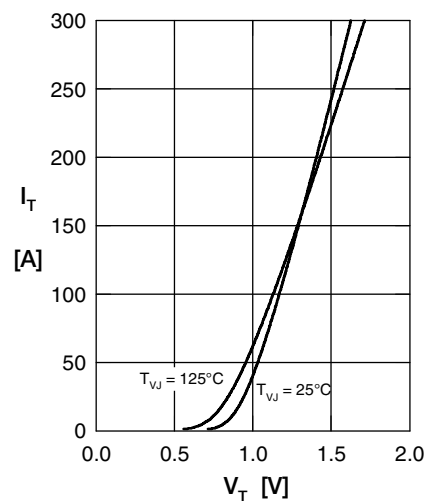


Fig. 5 Forward current I_T versus V_T

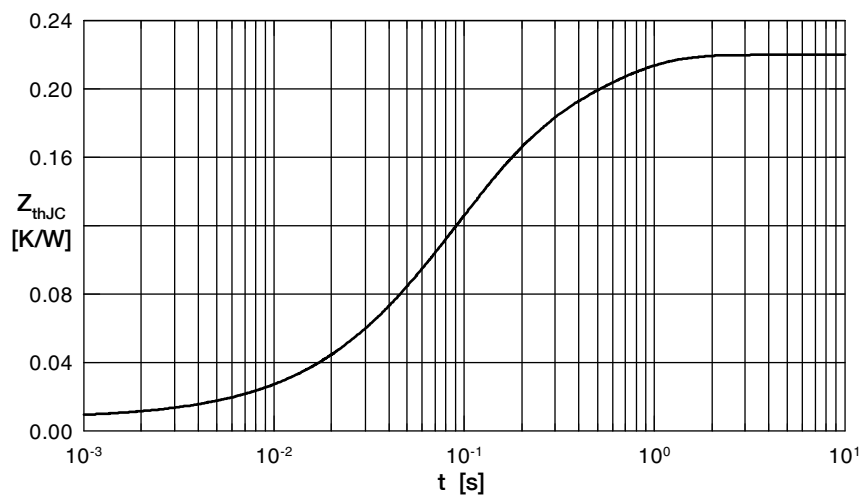


Fig. 6 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.0073	0.0001
2	0.0128	0.031
3	0.1329	0.084
4	0.067	0.42